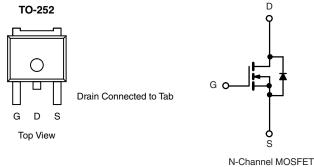


Vishay Siliconix

## Automotive N-Channel 150 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY      |  |  |  |  |
|----------------------|--|--|--|--|
| 150                  |  |  |  |  |
| 0.052                |  |  |  |  |
| 25                   |  |  |  |  |
| Configuration Single |  |  |  |  |
|                      |  |  |  |  |



#### FEATURES

- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- 100 % R<sub>g</sub> and UIS Tested
- AEC-Q101 Qualified
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



| ORDERING INFORMATION |                                 |                 |  |  |
|----------------------|---------------------------------|-----------------|--|--|
|                      | Package                         | TO-252          |  |  |
|                      | Lead (Pb)-free and Halogen-free | SQD25N15-52-GE3 |  |  |

| ABSOLUTE MAXIMUM RATINGS                     | (T <sub>C</sub> = 25 °C, unless | s otherwise noted                 | i)            |     |  |
|--|---------------------------------|-----------------------------------|---------------|-----|--|
| PARAMETER                                    | SYMBOL                          | LIMIT                             | UNIT          |     |  |
| Drain-Source Voltage                         | rain-Source Voltage             |                                   | 150           | V   |  |
| Gate-Source Voltage                          |                                 | V <sub>GS</sub>                   | ± 20          | v   |  |
| Continuous Drain Current                     | T <sub>C</sub> = 25 °C          | - I <sub>D</sub>                  | 25            |     |  |
|  | T <sub>C</sub> = 125 °C         |                                   | 16            |     |  |
| Continuous Source Current (Diode Conduction) | a                               | I <sub>S</sub>                    | 50            | А   |  |
| Pulsed Drain Current <sup>b</sup>            |                                 | I <sub>DM</sub>                   | 63            |     |  |
| Single Pulse Avalanche Current               | L = 0.1 mH                      | I <sub>AS</sub>                   | 30            |     |  |
| Single Pulse Avalanche Energy                | L = 0.1 MH                      | E <sub>AS</sub>                   | 45            | mJ  |  |
| Maximum Dawar Disainstian <sup>b</sup>       | T <sub>C</sub> = 25 °C          | D                                 | 107           | 144 |  |
| Maximum Power Dissipation <sup>b</sup>       | T <sub>C</sub> = 125 °C         | P <sub>D</sub>                    | 35            | W   |  |
| Operating Junction and Storage Temperature F | Range                           | T <sub>J</sub> , T <sub>stg</sub> | - 55 to + 175 | °C  |  |

| THERMAL RESISTANCE RATINGS |                        |                   |       |      |  |  |
|----------------------------|------------------------|-------------------|-------|------|--|--|
| PARAMETER                  |                        | SYMBOL            | LIMIT | UNIT |  |  |
| Junction-to-Ambient        | PCB Mount <sup>c</sup> | R <sub>thJA</sub> | 50    | °C/W |  |  |
| Junction-to-Case (Drain)   |                        | R <sub>thJC</sub> | 1.4   | C/W  |  |  |

Notes

c. When mounted on 1" square PCB (FR-4 material).

a. Package limited.

b. Pulse test; pulse width  $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%.$ 

SQD25N15-52

| PARAMETER   | SYMBOL                   | TEST CONDITIONS   |   | MIN. | TYP.  | MAX.  | UNI      |
|---|--------------------------|---|---|------|-------|-------|----------|
| Static  |                          |   |   |      |       |       |          |
| Drain-Source Breakdown Voltage  | V <sub>DS</sub>          | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \mu\text{A}$ |   | 150  | -     | -     | v        |
| Gate-Source Threshold Voltage   | V <sub>GS(th)</sub>      | $V_{DS} = V_{GS}, I_D = 250 \ \mu A$                    |   | 2.5  | 3     | 4     | v        |
| Gate-Source Leakage   | I <sub>GSS</sub>         | V <sub>DS</sub> =                                       | = 0 V, $V_{GS}$ = ± 20 V  | -    | -     | ± 100 | nA       |
|   |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = 150 V   | -    | -     | 1     |          |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>         | $V_{GS} = 0 V$  | $V_{DS} = 150 \text{ V}, \text{ T}_{\text{J}} = 125 ^{\circ}\text{C}$ | -    | -     | 50    | μA       |
|   |                          | $V_{GS} = 0 V$  | V <sub>DS</sub> = 150 V, T <sub>J</sub> = 175 °C                      | -    | -     | 250   |          |
| On-State Drain Current <sup>a</sup>   | I <sub>D(on)</sub>       | $V_{GS} = 10 V$   | $V_{DS} \ge 5 V$  | 30   | -     | -     | A        |
|   |                          | $V_{GS} = 10 V$   | I <sub>D</sub> = 15 A   | -    | 0.038 | 0.052 |          |
| Drain-Source On-State Resistance <sup>a</sup>   | R <sub>DS(on)</sub>      | $V_{GS} = 10 V$   | I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C                        | -    | -     | 0.104 | Ω        |
|   |                          | $V_{GS} = 10 \text{ V}$                                 | I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C                        | -    | -     | 0.136 |          |
| Forward Transconductanceb   | 9 <sub>fs</sub>          | V <sub>DS</sub>   | = 15 V, I <sub>D</sub> = 15 A   | -    | 33    | -     | S        |
| Dynamic <sup>b</sup>  |                          | ·   |   |      |       |       |          |
| Input Capacitance   | C <sub>iss</sub>         |   |   | -    | 1760  | 2200  | pF       |
| Output Capacitance  | C <sub>oss</sub>         | $V_{GS} = 0 V$  | V <sub>DS</sub> = 25 V, f = 1 MHz                                     | -    | 215   | 270   |          |
| Reverse Transfer Capacitance  | C <sub>rss</sub>         |   |   | -    | 80    | 100   |          |
| Total Gate Charge <sup>c</sup>  | Qg                       |   |   | -    | 34    | 51    | nC       |
| Gate-Source Charge <sup>c</sup>   | Q <sub>gs</sub>          | $V_{GS} = 10 V$   | $V_{DS} = 75 \text{ V}, \text{ I}_{D} = 25 \text{ A}$                 | -    | 14.5  | -     |          |
| Gate-Drain Charge <sup>c</sup>  | Q <sub>gd</sub>          |   |   | -    | 5.4   | -     |          |
| Gate Resistance   | Rg                       |   | f = 1 MHz   | 1    | 1.8   | 2.6   | Ω        |
| Turn-On Delay Time <sup>c</sup>   | t <sub>d(on)</sub>       |   |   | -    | 11    | 17    |          |
| Rise Time <sup>c</sup>  | t <sub>r</sub>           | V <sub>DD</sub>   | = 75 V, $R_L$ = 3 $\Omega$  | -    | 11    | 17    | ns       |
| Turn-Off Delay Time <sup>c</sup>  | t <sub>d(off)</sub>      |   | $V_{GEN} = 10 \text{ V}, \text{ R}_{g} = 1 \Omega$                    | -    | 20    | 30    |          |
| Fall Time <sup>c</sup>  | t <sub>f</sub>           | 7   | 1   |      | 6     | 9     | 1        |
| Source-Drain Diode Ratings and Char   | acteristics <sup>b</sup> | ·   |   |      |       |       |          |
| Pulsed Current <sup>a</sup>   | I <sub>SM</sub>          |   |   | -    | -     | 63    | A        |
| Forward Voltage   | V <sub>SD</sub>          | I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V            |   | -    | 0.87  | 1.5   | V        |
| <b>lotes</b><br>. Pulse test; pulse width $\leq$ 300 µs, duty c<br>. Guaranteed by design, not subject to p | ycle ≤ 2 %.              | 1   |   | 1    | 0.01  | 1.0   | <u>I</u> |

c. Independent of operating temperature.

www.vishay.com

SPECIFICATIONS (T<sub>C</sub> = 25 °C, unless otherwise noted)

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



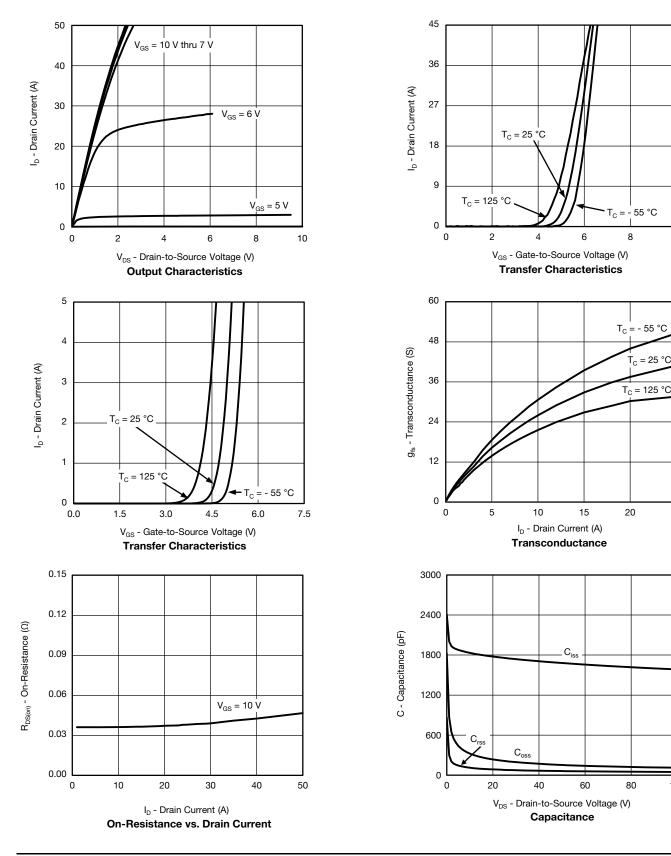
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10

25

100

#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



S12-2006-Rev. F, 20-Aug-12

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Document Number: 68604

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75 100 125

T<sub>J</sub> = 25 °C

6



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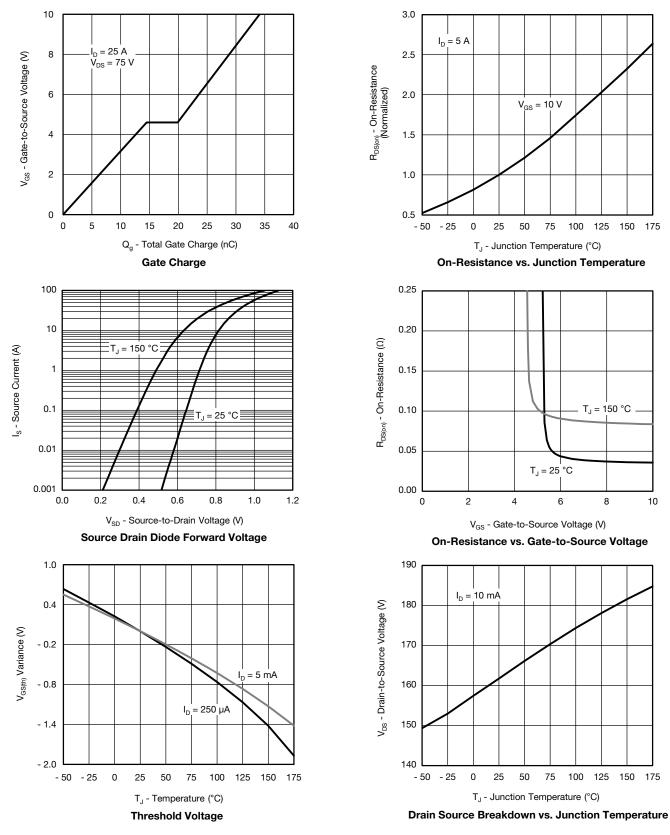
150 175

T<sub>J</sub> = 150 °C

8

10

#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Document Number: 68604

75 100 125 150 175

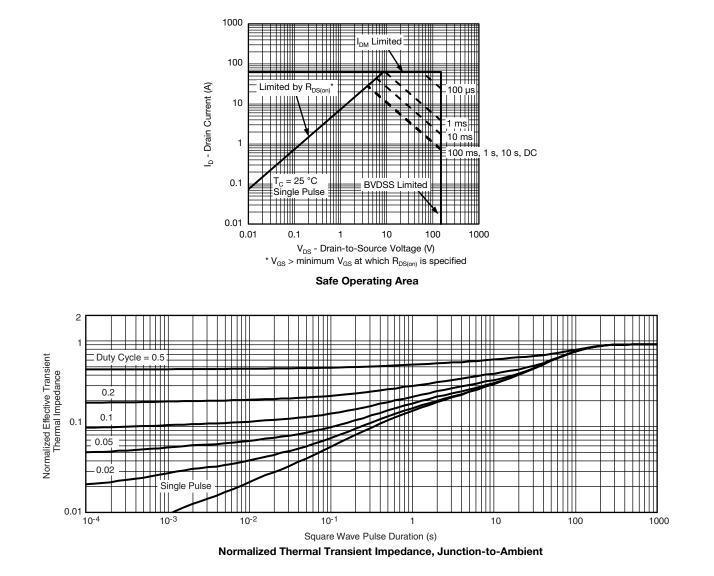
S12-2006-Rev. F, 20-Aug-12

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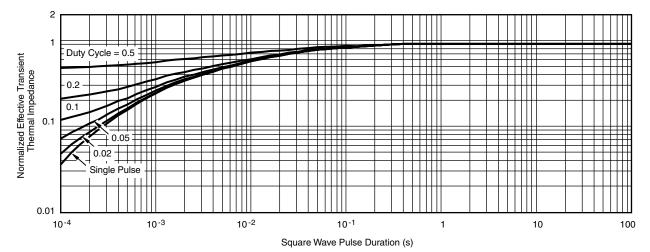
#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)





### **Vishay Siliconix**

#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

- Normalized Transient Thermal Impedance Junction-to- Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?68604">www.vishay.com/ppg?68604</a>.

The characteristics shown in the two graphs



## **DPAK / TO-252 and Reverse DPAK**

Ordering codes for the SQ rugged series power MOSFETs in the DPAK / TO-252 and Reverse DPAK packages:

| DATASHEET PART NUMBER | OLD ORDERING CODE <sup>a</sup> | NEW ORDERING CODE  |
|-----------------------|--------------------------------|--------------------|
| SQD07N25-350H         | SQD07N25-350H-GE3              | SQD07N25-350H_GE3  |
| SQD100N03-3m2L        | SQD100N03-3M2L-GE3             | SQD100N03-3M2L_GE3 |
| SQD100N03-3m4         | SQD100N03-3M4-GE3              | SQD100N03-3M4_GE3  |
| SQD100N04-3m6         | SQD100N04-3M6-GE3              | SQD100N04-3M6_GE3  |
| SQD100N04-3m6L        | SQD100N04-3M6L-GE3             | SQD100N04-3M6L_GE3 |
| SQD10N30-330H         | SQD10N30-330H-GE3              | SQD10N30-330H_GE3  |
| SQD15N06-42L          | SQD15N06-42L-GE3               | SQD15N06-42L_GE3   |
| SQD19P06-60L          | SQD19P06-60L-GE3               | SQD19P06-60L_GE3   |
| SQD23N06-31L          | SQD23N06-31L-GE3               | SQD23N06-31L_GE3   |
| SQD25N06-22L          | SQD25N06-22L-GE3               | SQD25N06-22L_GE3   |
| SQD25N15-52           | SQD25N15-52-GE3                | SQD25N15-52_GE3    |
| SQD30N05-20L          | SQD30N05-20L-GE3               | SQD30N05-20L_GE3   |
| SQD40N06-14L          | SQD40N06-14L-GE3               | SQD40N06-14L_GE3   |
| SQD40N10-25           | SQD40N10-25-GE3                | SQD40N10-25_GE3    |
| SQD40P10-40L          | SQD40P10-40L-GE3               | SQD40P10-40L_GE3   |
| SQD45P03-12           | SQD45P03-12-GE3                | SQD45P03-12_GE3    |
| SQD50N04-5m6          | SQD50N04-5M6-GE3               | SQD50N04-5M6_GE3   |
| SQD50N05-11L          | SQD50N05-11L-GE3               | SQD50N05-11L_GE3   |
| SQD50N06-09L          | SQD50N06-09L-GE3               | SQD50N06-09L_GE3   |
| SQD50N10-8m9L         | SQD50N10-8M9L-GE3              | SQD50N10-8M9L_GE3  |
| SQD50P03-07           | SQD50P03-07-GE3                | SQD50P03-07_GE3    |
| SQD50P04-13L          | SQD50P04-13L-GE3               | SQD50P04-13L_GE3   |
| SQD50P04-09L          | SQD50P04-09L-GE3               | SQD50P04-09L_GE3   |
| SQD50P06-15L          | SQD50P06-15L-GE3               | SQD50P06-15L_GE3   |
| SQD50P08-25L          | SQD50P08-25L-GE3               | SQD50P08-25L_GE3   |
| SQD50P08-28           | SQD50P08-28-GE3                | SQD50P08-28_GE3    |
| SQD90P04-9m4L         | SQD90P04-9M4L-GE3              | SQD90P04-9M4L_GE3  |
| SQD97N06-6m3L         | SQD97N06-6M3L-GE3              | SQD97N06-6M3L_GE3  |
| SQR40N10-25           | SQR40N10-25-GE3                | SQR40N10-25_GE3    |
| SQR50N04-3m8          | SQR50N04-3M8-GE3               | SQR50N04-3M8 GE3   |

Note

a. Old ordering code is obsolete and no longer valid for new orders

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Е b3 Ľ Δ ŝ b2 e1 Б E1

# C2 т gage plane height (0.5 mm)

-C

- A1

**TO-252AA** Case Outline

|  | MILLIN | <b>IETERS</b> | INC       | HES   |  |
|--|--------|---------------|-----------|-------|--|
| DIM.   | MIN.   | MAX.          | MIN.      | MAX.  |  |
| А  | 2.18   | 2.38          | 0.086     | 0.094 |  |
| A1   | -      | 0.127         | -         | 0.005 |  |
| b  | 0.64   | 0.88          | 0.025     | 0.035 |  |
| b2   | 0.76   | 1.14          | 0.030     | 0.045 |  |
| b3   | 4.95   | 5.46          | 0.195     | 0.215 |  |
| С  | 0.46   | 0.61          | 0.018     | 0.024 |  |
| C2   | 0.46   | 0.89          | 0.018     | 0.035 |  |
| D  | 5.97   | 6.22          | 0.235     | 0.245 |  |
| D1   | 4.10   | -             | 0.161     | -     |  |
| Е  | 6.35   | 6.73          | 0.250     | 0.265 |  |
| E1   | 4.32   | -             | 0.170     | -     |  |
| Н  | 9.40   | 10.41         | 0.370     | 0.410 |  |
| е  | 2.28   | BSC           | 0.090 BSC |       |  |
| e1   | 4.56   | 4.56 BSC      |           | BSC   |  |
| L  | 1.40   | 1.78          | 0.055     | 0.070 |  |
| L3   | 0.89   | 1.27          | 0.035     | 0.050 |  |
| L4   | -      | 1.02          | -         | 0.040 |  |
| L5   | 1.01   | 1.52          | 0.040     | 0.060 |  |
| ECN: T13-0592-Rev. A, 02-Sep-13<br>DWG: 6019 |        |               |           |       |  |

Note

• Dimension L3 is for reference only.





#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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